EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1595	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:19
L2	227	(438/747).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:19
L3	321	(257/e21.553).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:19
L4	759	wet adj etch$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/26 10:20
L5	39	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and foreign	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/26 10:20
L7	4431	SUZUKI-AKIRA .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:24
L8	283	NOMA-TAKASHI .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:24
L9	39	SHINOGI-HIROYUKI .in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:24

L15	9	"5994204"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/26 10:47
L16	2589	438/455	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/26 10:47
L17	174	TAKAO-YUKIHIRO.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/26 10:47
S1	19464	groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:02
S2	1159	etch$3 near groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:42
S3	4727	etch$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:42
S4	346	wet adj etch$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/27 13:44
S5	559	wet adj etch$3 with groove and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/26 10:20

S6	175	wet adj etch$3 with groove and wafer and semiconductor and spin$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:43
S7	26	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and foreign	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/26 10:20
S8	28	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and particles	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:47
S9	1	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and round with corners	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/27 13:48
S10	4	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and round$3 with corner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/12/26 10:20
S11	1	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and rounding with corner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:45
S12	4	wet adj etch$3 with groove and wafer and semiconductor and spin$4 and rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:47
S13	23	support with substrate and wet adj etch$3 with groove and wafer and semiconductor and spin$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52

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S14	41	support with substrate and wet with etch$3 with groove and wafer and semiconductor and spin$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:48
S15	74	support with substrate and wet with etch$3 same groove and wafer and semiconductor and spin$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:48
S16	1	support with substrate and wet adj etch$3 with groove and wafer and semiconductor and rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52
S17	23	support with substrate and wet adj etch$3 with groove and wafer and semiconductor and round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/28 03:52
S18	5963	groove same etch$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:22
S19	1159	groove near etch$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:22
S20	25	groove near etch$3 same round$3 and wafer and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:41
S21	3	groove near etch$3 same round$3 and wafer and semiconductor and support$3 with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:30

S22	10	groove near etch$3 same round$3 and wafer and semiconductor and wet with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:32
S23	1	groove near wet near etch$3 same round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:42
S24	7	trench near wet near etch$3 same round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:44
S25	0	trench near wet near etch$3 same round$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:45
S26	6	trench with wet near etch$3 same round$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:53
S27	7	(trench or groove) with wet near etch$3 same round$3 and support with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:54
S28	4	(trench or groove) and wet near etch$3 with round$3 and support with substrate and damage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:56
S29	82	wet near etch$3 with round$3 and damage	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 09:57

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S30	92	wet near etch$3 with round$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:02
S31	63	wet near etch$3 with round$3 and spin$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:03
S32	1	wet near etch$3 with round$3 and spin$4 same revers$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:03
S33	186	wet near etch$3 and spin$4 same revers$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:04
S34	104	wet near etch$3 and spin$4 same revers$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:04
S35	1	wet near etch$3 and spin$4 same revers$3 and damage with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:05
S36	6	wet near etch$3 and spin$4 same revers$3 and residue with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S37	10	wet with etch$3 and spin$4 same revers$3 and residue with removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08

S38	153	wet with etch$3 and spin$4 same revers$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:08
S39	3	wet with etch$3 and spin$4 near revers$3 and removal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:10
S40	1	wet with etch$3 same spin$4 near revers$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 10:54
S41	1207	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:12
S42	206	(438/747).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:19
S43	244	microbalance and heater	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:12
S44	77	microbalance and heater and organic and detection	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:15
S45	63	microbalance and heater and organic and detection and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/28 15:15

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S46	679757	thinning with substrate same groove and wet etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/05/27 15:26
S47	34	thinning with substrate same groove and wet etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/05/27 15:26
S48	551017	corner rounding with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/16 18:51
S49	178	corner rounding with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:51
S50	0	corner rounding with etch$3 with groove	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:52
S51	61	trench with corner rounding with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:52
S52	0	trench with corner rounding with etch$3 with known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:52
S53	3	trench with corner rounding with etch$3 same known	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:55

S54	16	semiconductor with corner rounding with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 18:58
S55	1	semiconductor wafer with corner rounding with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 19:18
S56	2	semiconductor wafer with corner rounding	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	OFF	2006/11/16 19:19
S57	25	wafer with corner rounding and trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/11/16 19:28
S58	30	semiconductor wafer with (groove or trench) and (groove or trench) with corner round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 22:58
S59	30	semiconductor wafer with (groove or trench) and (groove or trench) with corner round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:37
S60	42	semiconductor wafer same (groove or trench) and (groove or trench) with corner round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:25
S61	6	semiconductor wafer same (groove or trench) and (groove or trench) with corner round$3 same wet with etch$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:26

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S62	21	"6150234"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/03/18 23:37
S63	3263	groove same etch$3 and wafer and semiconductor and bond$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:03
S64	38	groove same etch$3 and wafer and semiconductor and bond$3 and corner with round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:14
S65	81	groove same etch$3 and wafer and semiconductor and bond$3 and (corner or edge)with round$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 16:14
S66	15	groove same etch$3 and wafer and semiconductor and bond$3 and (corner or edge)with round$3 same (wet with etch$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 17:39
S67	2	("20020013061").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 17:53
S68	84	glass substrate same bonding same semiconductor wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 17:55
S69	21	glass substrate same bonding same semiconductor wafer and wiring	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:42

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S70	109	spinning same HF same etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:43
S71	1013	spin$4 same HF same etch$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:43
S72	5	spin$4 same HF same etch$3 same (corner or edge) with round$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:44
S73	21	spin$4 same HF same etch$3 same revers$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:46
S74	3	spin$4 with etch$3 same HF same revers$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:47
S75	345	spin$4 with etch$3 same HF	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:47
S76	22	spin$4 with etch$3 same HF and trench and semiconductor wafer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:48

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S77	6	spin$4 with etch$3 same HF and trench and semiconductor wafer and revers$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/08/03 18:48
S78	1535	(438/745).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:19
S79	221	(438/747).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/03 19:13
S80	309	(257/e21.553).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/26 10:19